

Lateral power MOSFET having metal strap layer to reduce distributed resistance and method of fabricating the same

Patent Number: EP0720225

Publication date: 1996-07-03

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Requested Patent: EP0720225, A3

Application Number: EP19950309533 19951229

Priority Number(s): US19940367388 19941230

IPC Classification: H01L23/482; H01L23/528; H01L29/78

EC Classification: H01L23/482E, H01L29/10D2B2B, H01L29/417D4, H01L29/78B2C

Equivalents: JP8264785, US5767546

Cited Documents: DE4037876; US5355008; US3667008; EP0624909

Abstract

To reduce the distributed resistance in an integrated circuit die, a relatively thick metal strap layer is deposited on a bus or other conductive path in the top metal layer. The metal strap layer is formed by etching a longitudinal channel in the passivation layer over the bus and plating a thick metal layer, preferably nickel, in the channel. The metal strap layer dramatically reduces the resistance of the bus.

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